

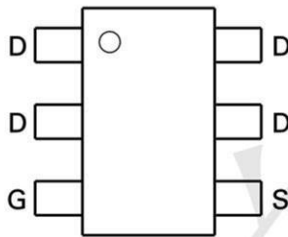
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-30V	60mΩ@-10 V	-4.1A
	87mΩ@-4.5V	

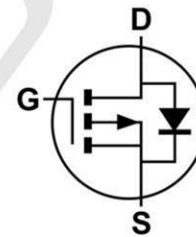
Application

- DC-DC Converters.
- Load Switch.
- Power Management.

Package and Pin Configuration



Circuit diagram



Equivalent Circuit

Marking: **P 3P5**

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

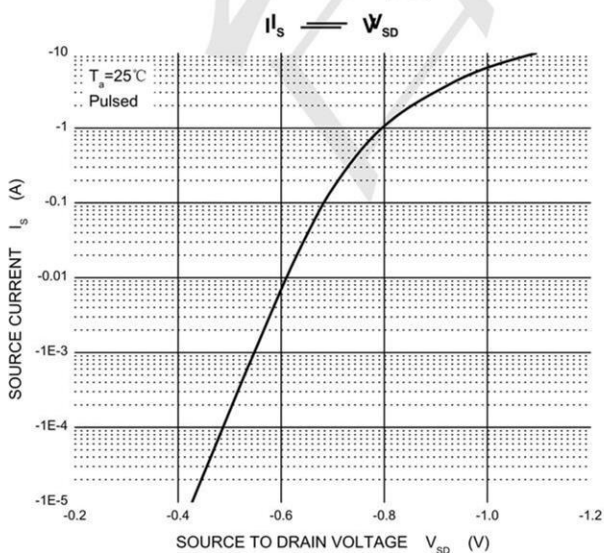
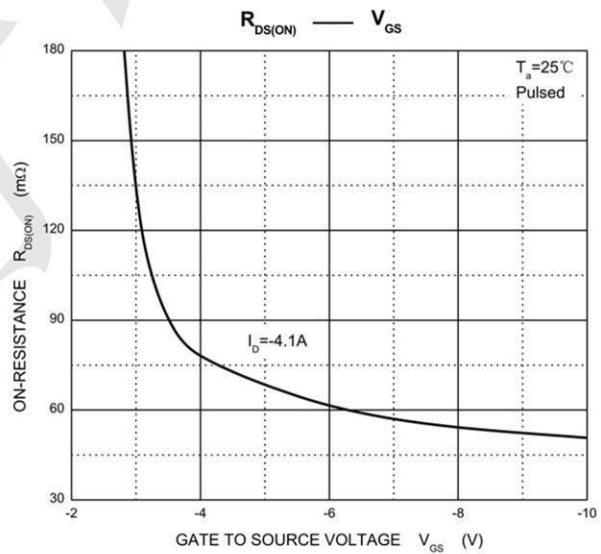
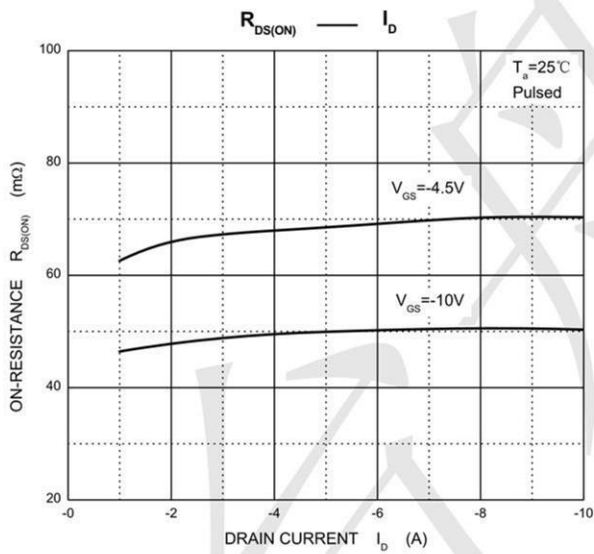
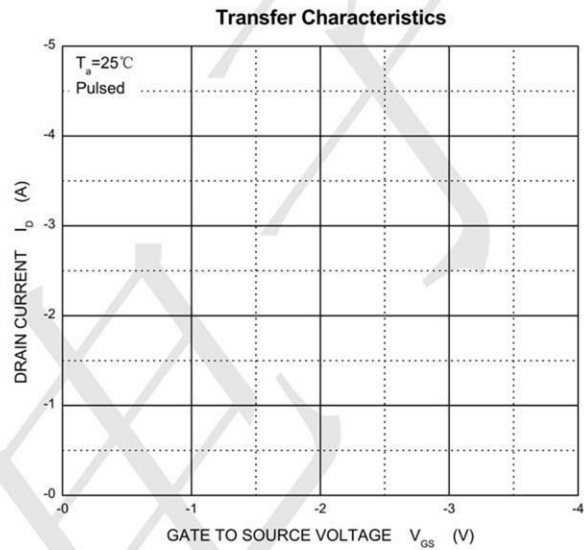
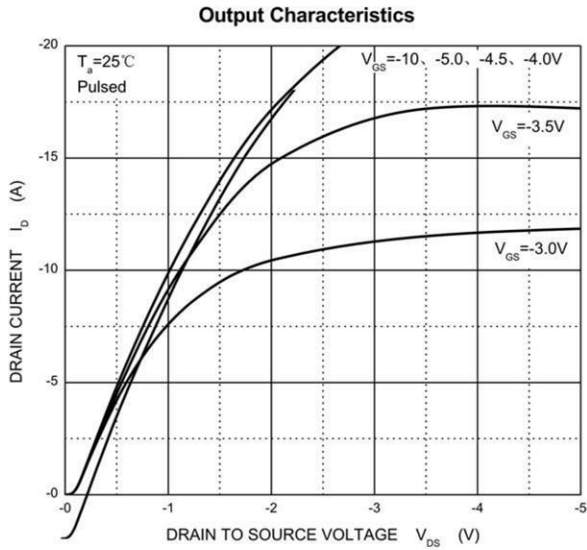
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-4.1	A
Power Dissipation	P_D	350	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

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Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -24V, V_{GS} = 0V$			-1	μA
Gate-source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Drain-source on-resistance (note 1)	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -4.1A$		50	60	m Ω
		$V_{GS} = -4.5V, I_D = -3A$		68	87	m Ω
Forward transconductance (note 1)	g_{fs}	$V_{DS} = -5V, I_D = -4A$	5.5			S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1	-1.4	-3	V
Diode forward voltage (note 1)	V_{SD}	$I_S = -1A, V_{GS} = 0V$			-1	V
Dynamic characteristics (note 2)						
Input capacitance	C_{iss}	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$		700		pF
Output capacitance	C_{oss}			120		pF
Reverse transfer capacitance	C_{rss}			75		pF
Switching Characteristics (note 2)						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = -10V, V_{DS} = -15V,$ $R_L = 3.6\Omega, R_{GEN} = 3\Omega$		8.6		ns
Turn-on rise time	t_r			5.0		ns
Turn-off delay time	$t_{d(off)}$			28.2		ns
Turn-off fall time	t_f			13.5		ns

Typical Performance Characteristics ($T_A=25^\circ\text{C}$ unless otherwise Specified)





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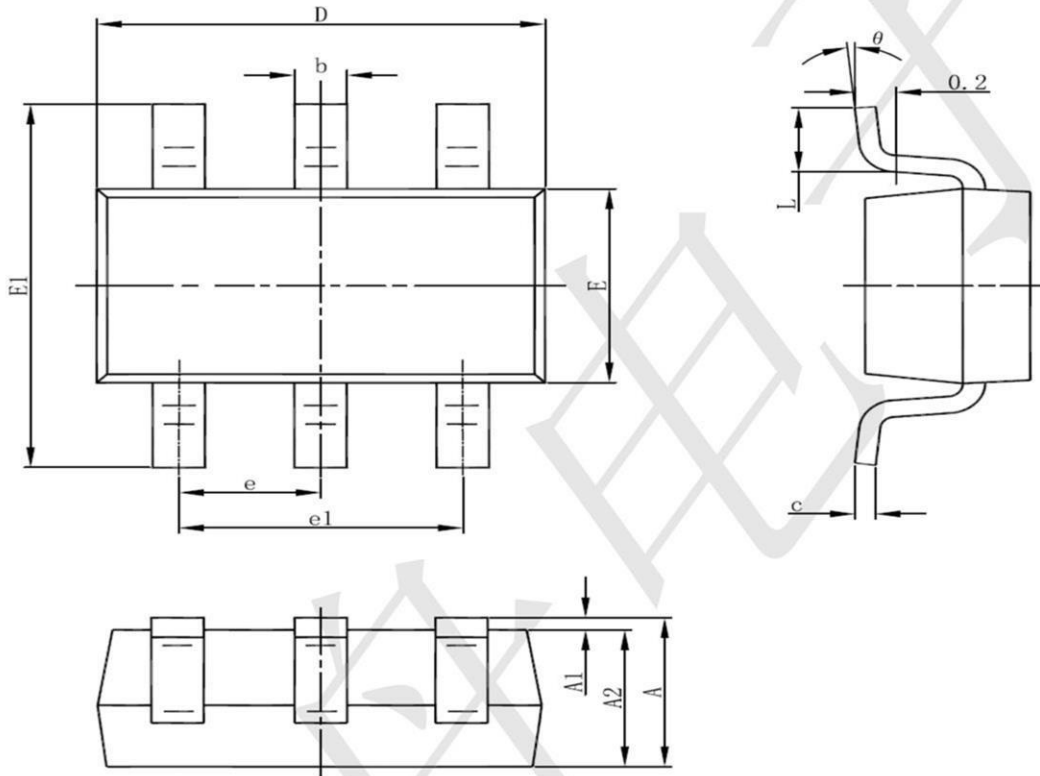
—台丹电子—

FDC658AP

30V P-CHANNEL ENHANCEMENT MODE MOSFET

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SOT23-6 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°